

Red Chip--ORT008URV

1. Scope:

- This specification applies to Gap/InGaAlP/GaAs LED chips.

2. Structure:

- Mesa Type: smooth surface.
- Electrodes:
P (Anode) Side: gold alloy.
N (Cathode) Side: gold alloy.

3. Size:

- Top Size: $130\mu\text{m}\times 130\mu\text{m} \pm 20\mu\text{m}$; Bottom Size: $155\mu\text{m}\times 155\mu\text{m} \pm 20\mu\text{m}$
- Chip Height: $100\mu\text{m} \pm 30\mu\text{m}$
- Pad Size: $90\mu\text{m} \pm 10\mu\text{m}$
- Pattern Drawing: fig.1.

4. Electro-Optical Characteristics:

($T_a=+25^\circ\text{C}$)

Parameter	Symbol	Unit	Min	Typ	Max	Test Condition
Forward voltage	V_F	V		2.15	2.25	$I_F=20\text{mA}$
Reverse current	I_R	μA			30	$V_R=5\text{V}$
Dominant wavelength	λ_d	nm	620		630	$I_F=20\text{mA}$
Luminous Intensity	I_v	mcd	25	55		$I_F=20\text{mA}$

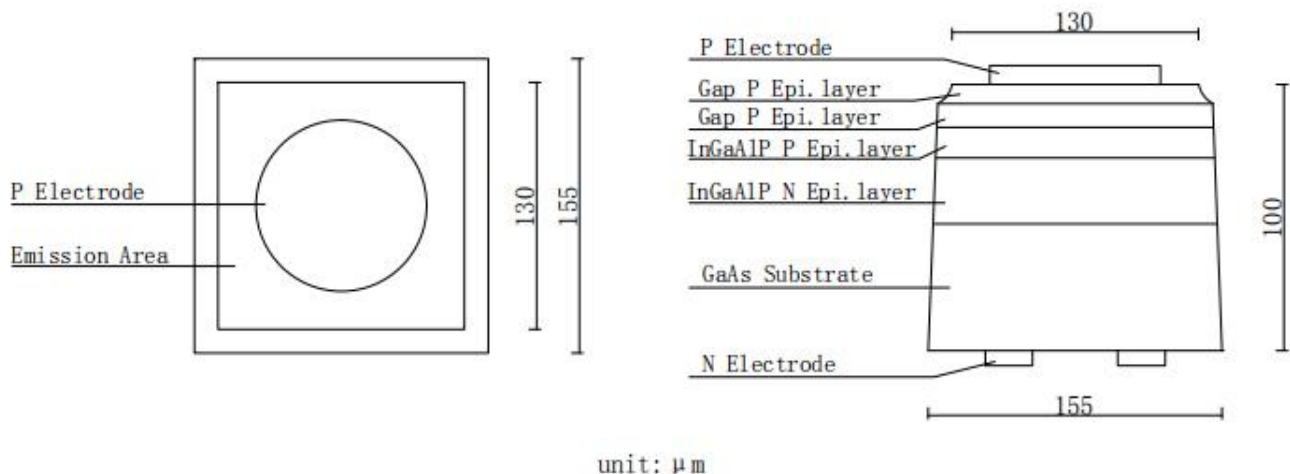


fig.1

5. Packing and Labeling:

- Packing: Sheet Type
- Each pellet is mounted on an adhesive sheet with wire-bonded electrode side up.
- Labeling: Each lot has a label sheet、 writing Type、 Lot No、 Pcs、 Avg P_o 、 V_F 、 W_{lp} and quantity of good chips.



6. Application Notes:

- All data are measured by Orient' s tester on bare chips within 98% of the nominal value.
- Measurement error for dominant wavelength and peak wavelength is $\pm 5\text{nm}$